






- (97) ((float\$3 adj gate) same (control adj gate)) same (((ba
- (10) (((float\$3 adj gate) same (control adj gate)) same (((ba
- (10) (((float\$3 adj gate) same (control adj gate)) same (((ba
- (173565) metal adj oxide
- (10) (((float\$3 adj gate) same (control adj gate)) same (((ba
- (387) ((float\$3 adj gate) same (control adj gate)) and (((ba
- (1) (((float\$3 adj gate) same (control adj gate)) and (((ba
- (31) ((float\$3 adj gate) same (control adj gate)) and (ald (at
- (9) (((barrier adj height) (energy adj band))) near2 (asymme
- (41) (((float\$3 adj gate) same (control adj gate)) same (((b
- (49) (((barrier adj height) (energy adj band))) near2 (asymr
- (49) (((barrier adj height) (energy adj band))) near2 (asymr
- (4453) depletion adj mode
- (2) (((barrier adj height) (energy adj band))) near2 (asymn

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DBs: USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB

Default operator: ☐ OR


☒ Plurals

☒ Highlight all hit terms initially

(((barrier adj height) (energy adj band))) near2 (asymmet\$4 differen\$2) and (float\$3 adj gate) and (control adj gate)) (((float\$3 adj gate) same (control adj gate)) same (((barrier near (height tunnel)) (energy diagram) near band)) (work adj function)) and (metal adj oxide) (((float\$3 adj gate) same (control adj gate)) and (ald (atomic adj layer adj deposit\$3))))

Feb 202



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8	<input type="checkbox"/>	<input type="checkbox"/>	Ahn, Kie Y. et al.	US 20020086556 A1	20020704	11	Methods of forming silicon-doped aluminum oxide, and methods of forming transistors and memory devices	438/785		

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